

N-channel 800 V, 0.470 Ω typ., 9 A MDmesh™ K5 Power MOSFET in a TO-220FP package

Datasheet - production data

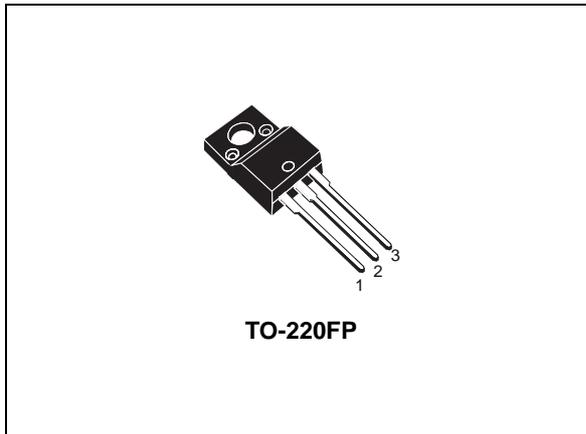
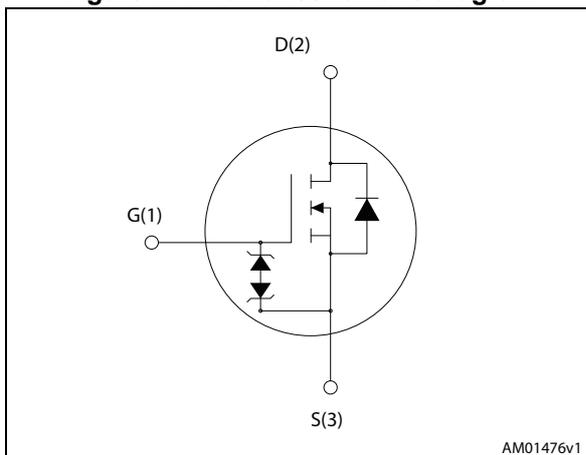


Figure 1. Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D	P_{TOT}
STF10N80K5	800 V	0.600 Ω	9 A	30 W

- Industry's best $R_{DS(on)}$
- Industry's best figure of merit (FoM)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1. Device summary

Order code	Marking	Package	Packaging
STF10N80K5	10N80K5	TO-220FP	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Units
V_{GS}	Gate-source voltage	± 30	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	9	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	6	A
$I_{DM}^{(2)}$	Drain current (pulsed)	36	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	30	W
I_{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T_{jmax})	3	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$)	130	mJ
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ }^\circ\text{C}$)	2500	V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	V/ns
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. Limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 9\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DS(Peak)} \leq V_{(BR)DSS}$
4. $V_{DS} \leq 640\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Units
$R_{thj-case}$	Thermal resistance junction-case max	4.2	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	800			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 800\text{ V}$			1	μA
		$V_{GS} = 0, V_{DS} = 800\text{ V}, T_C = 125\text{ °C}$			50	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0, V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$		0.470	0.600	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	635	-	pF
C_{oss}	Output capacitance		-	53	-	pF
C_{rss}	Reverse transfer capacitance		-	0.8	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0, V_{DS} = 0\text{ to }640\text{ V}$	-	85	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	34	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0$	-	6	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}, I_D = 9\text{ A}$ $V_{GS} = 10\text{ V}$ (see Figure 16)	-	22	-	nC
Q_{gs}	Gate-source charge		-	5.5	-	nC
Q_{gd}	Gate-drain charge		-	13.2	-	nC

1. "Time related" is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. "Energy related" is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 4.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 18)	-	14.5	-	ns
t_r	Rise time		-	11	-	ns
$t_{d(off)}$	Turn-off delay time		-	35	-	ns
t_f	Fall time		-	14	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		9	A
I_{SDM}	Source-drain current (pulsed)		-		36	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 9\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, (see Figure 17)	-	370		ns
Q_{rr}	Reverse recovery charge		-	4.58		μC
I_{RRM}	Reverse recovery current		-	25		A
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17)	-	520		ns
Q_{rr}	Reverse recovery charge		-	5.88		μC
I_{RRM}	Reverse recovery current		-	22.5		A

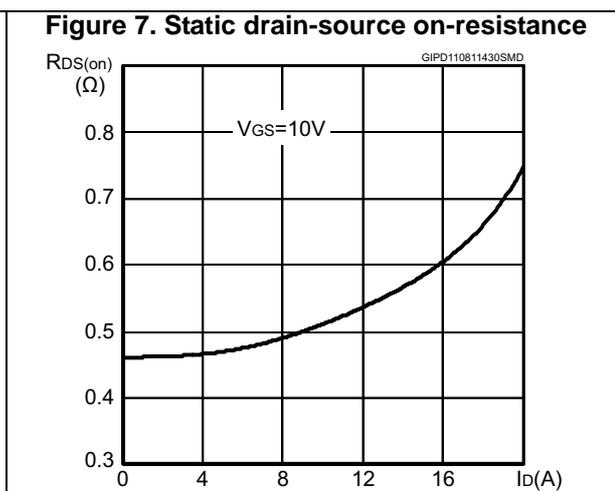
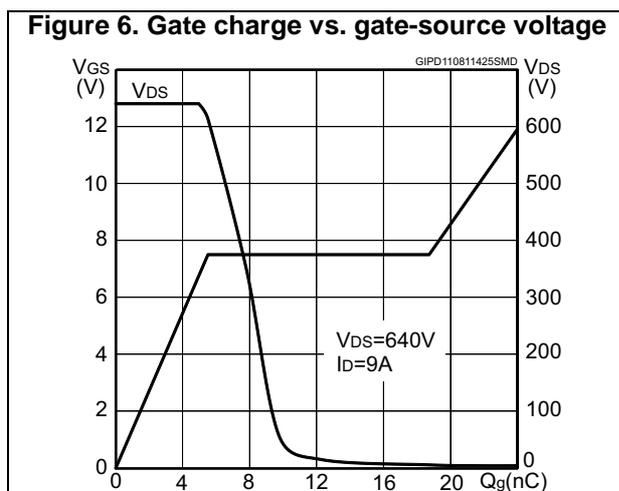
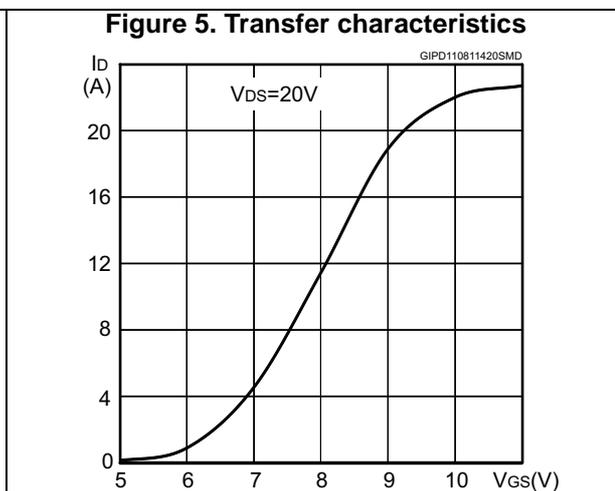
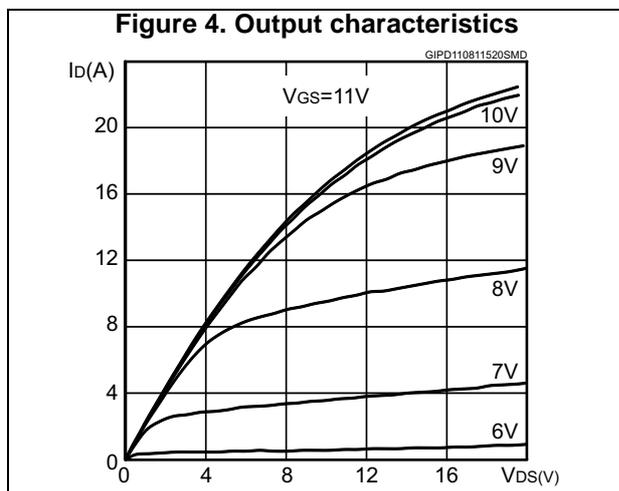
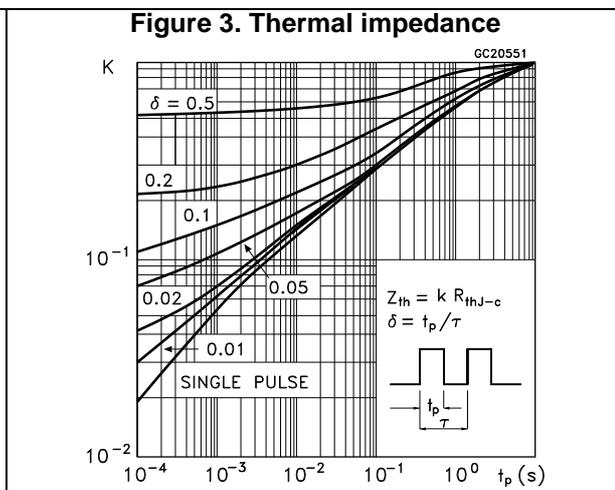
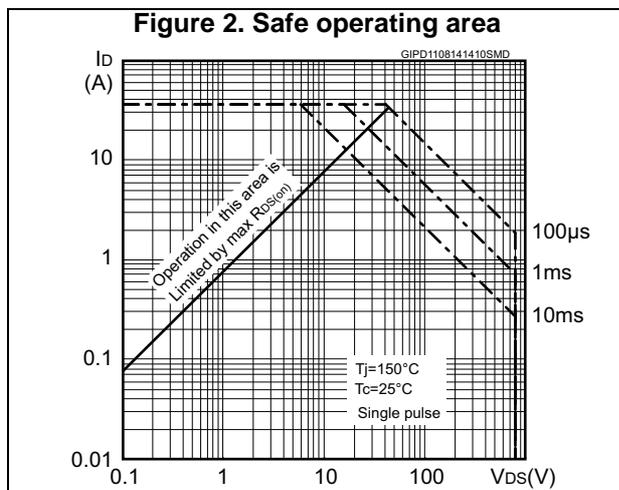
1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0$	30	-	-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance the ESD capability of the device. The Zener voltage is appropriate for efficient and cost-effective intervention to protect the device integrity. These integrated Zener diodes thus eliminate the need for external components.

3 Electrical characteristics (curves)



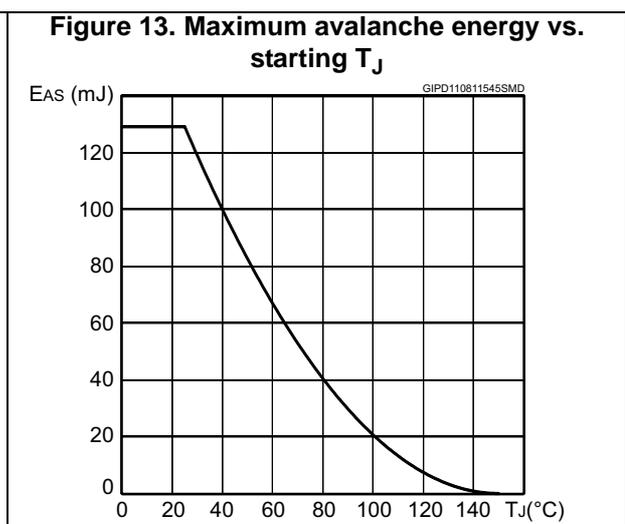
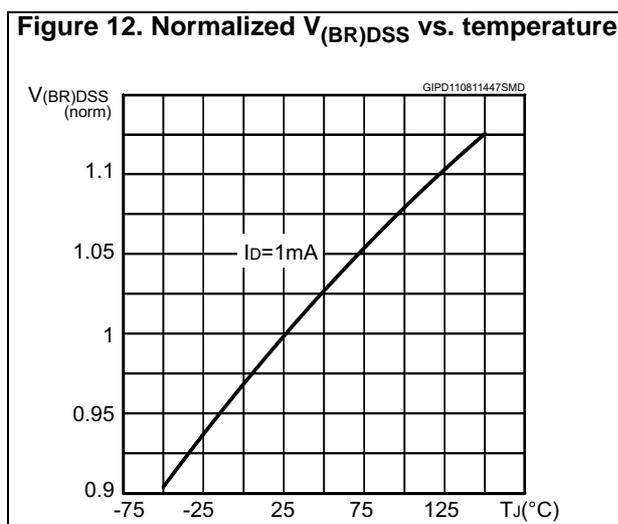
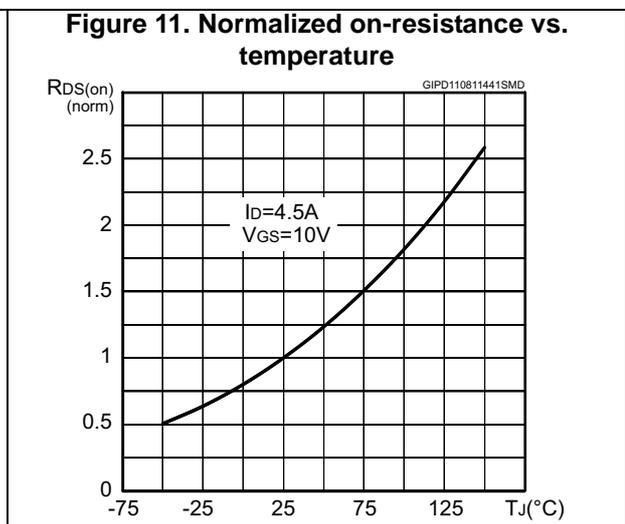
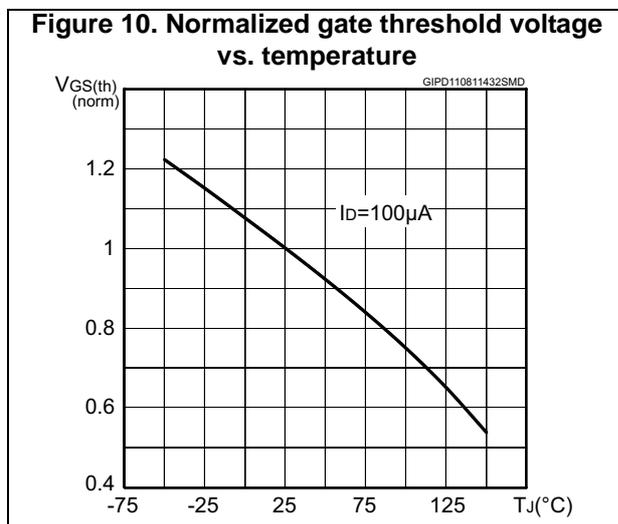
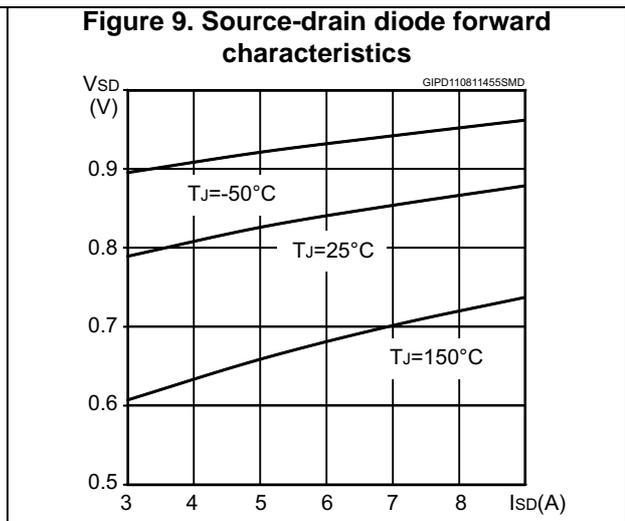
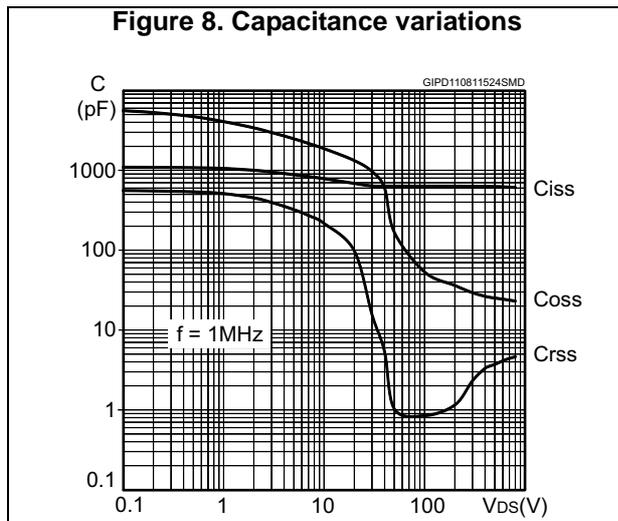
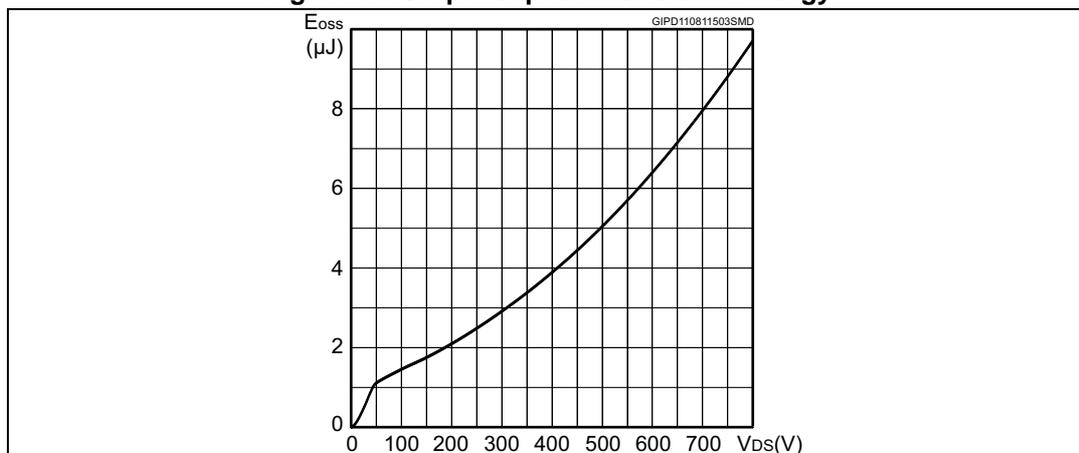
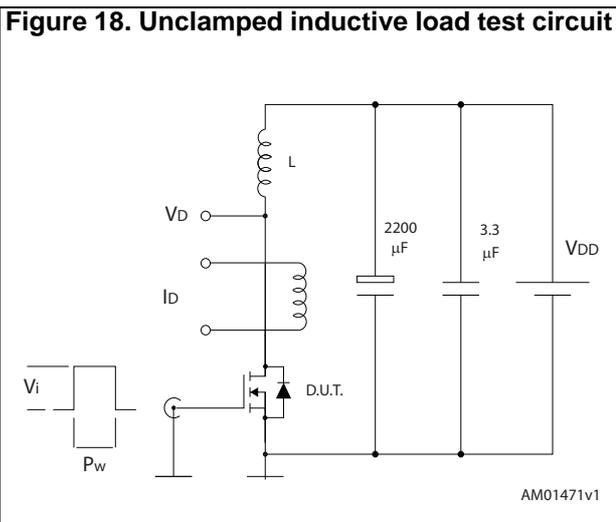
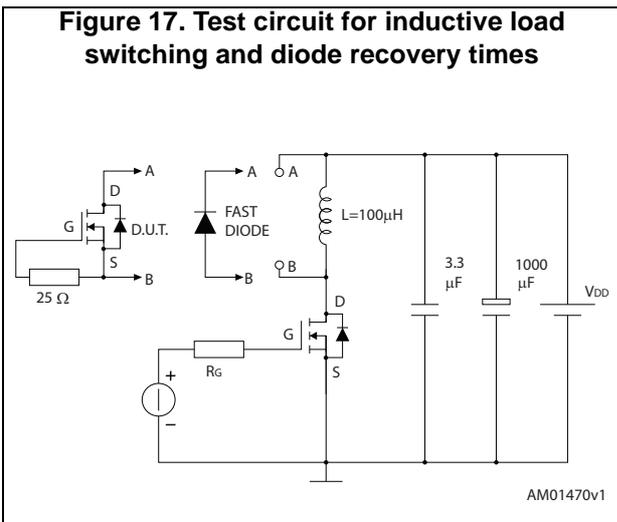
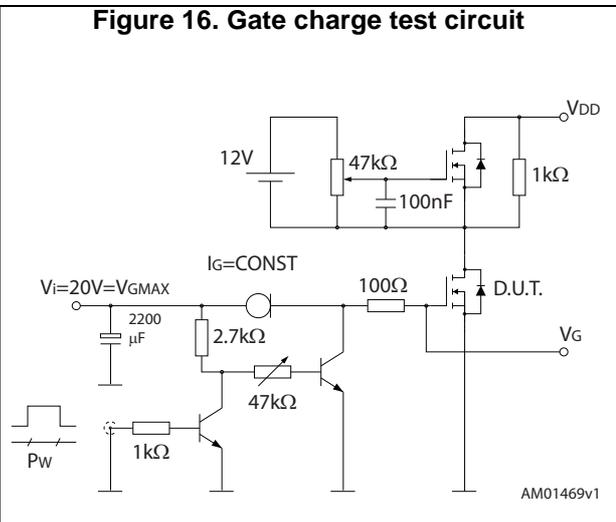
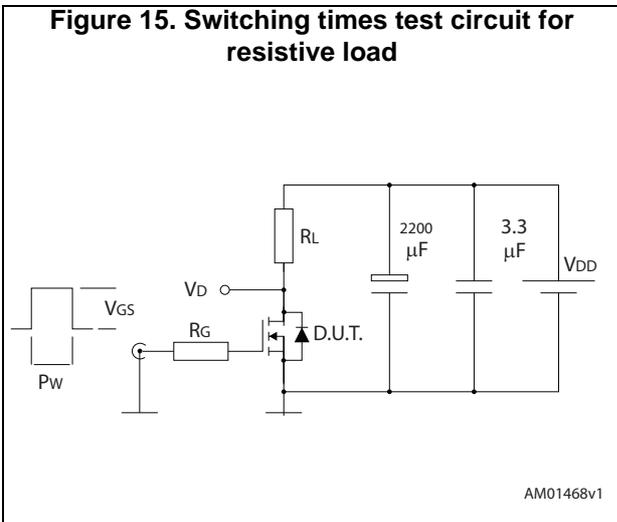


Figure 14. Output capacitance stored energy



4 Test circuits



5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 19. TO-220FP drawing

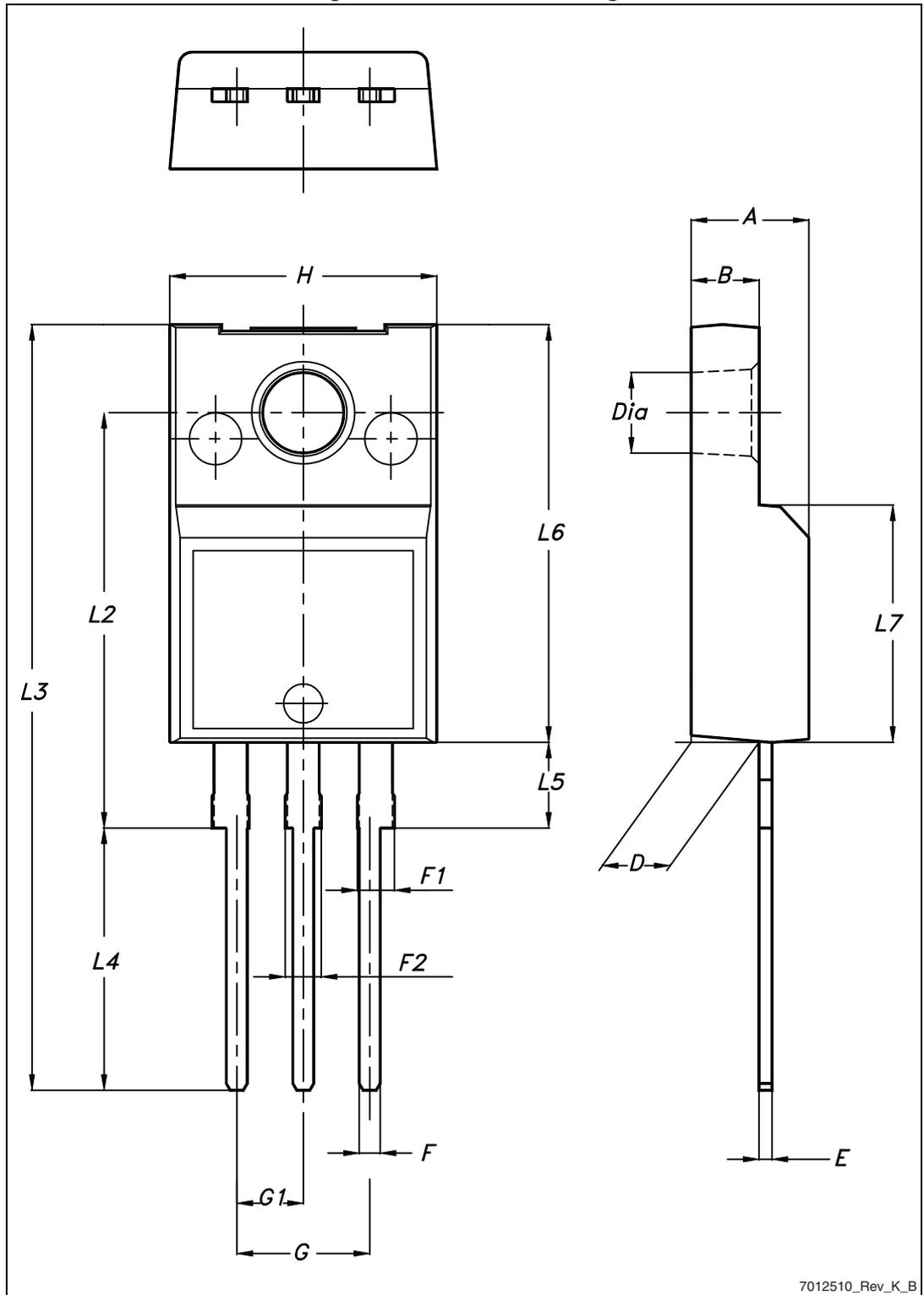


Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

6 Revision history

Table 10. Document revision history

Date	Revision	Changes
23-Jun-2014	1	Initial release.
13-Aug-2014	2	<ul style="list-style-type: none">– Document status promoted from preliminary data to production data.– Inserted Section 3: Electrical characteristics (curves).– Minor text changes.
17-Set-2014	3	Updated title, features and description in cover page.
05-Nov-2014	4	<ul style="list-style-type: none">Updated 3: Electrical characteristics (curves)Minor text changes

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